

**In the Claims**

**Claims pending in the application are as follows:**

1 1.-24. (canceled)

1 25. (currently amended) A method of etching a layer ~~form~~from a surface of a wafer  
2 comprising the steps of:

3 providing an etchant fluid;

4 providing at least one fluid immiscible with the etchant fluid having a different density  
5 than the etchant fluid and forming a fluid interface therebetween;

6 positioning a wafer in the etchant fluid to facilitate etching of a layer on the wafer; and  
7 terminating etching of the wafer when the wafer is passed through the fluid interface

8 into the at least one fluid immiscible with the etchant fluid.

1 26. (Previously presented) The method of claim 25 wherein the step of providing at  
2 least one fluid immiscible with the etchant fluid comprises providing two fluids  
3 immiscible with the etchant fluid, both fluids having a lower density than the etchant fluid  
4 and immiscible with each other such that a first fluid interface exists between the two  
5 fluids and the etchant fluid and a second fluid interface exists between the two fluids.

1 27. (Previously presented) The method of claim 26 wherein the step of terminating  
2 etching of the surface layer comprises passing the wafer through the first fluid interface  
3 into one of the two fluids.

1 28. (Previously presented) The method of claim 26 wherein the step of terminating  
2 etching of the surface layer comprises drawing the wafer through the first fluid interface to  
3 provide a rapid etch stop and further including the step of passing the wafer through the  
4 second fluid interface such that a protective coating is formed on a surface of the wafer.

1 29. (canceled)

1 30. (canceled)